PARA LIGHT ELECTRONICS CO., LTD.
4F, No.1, Lane 93, Chien Yi Road, Chung Ho City, Taipei, Taiwan, R.O.C.

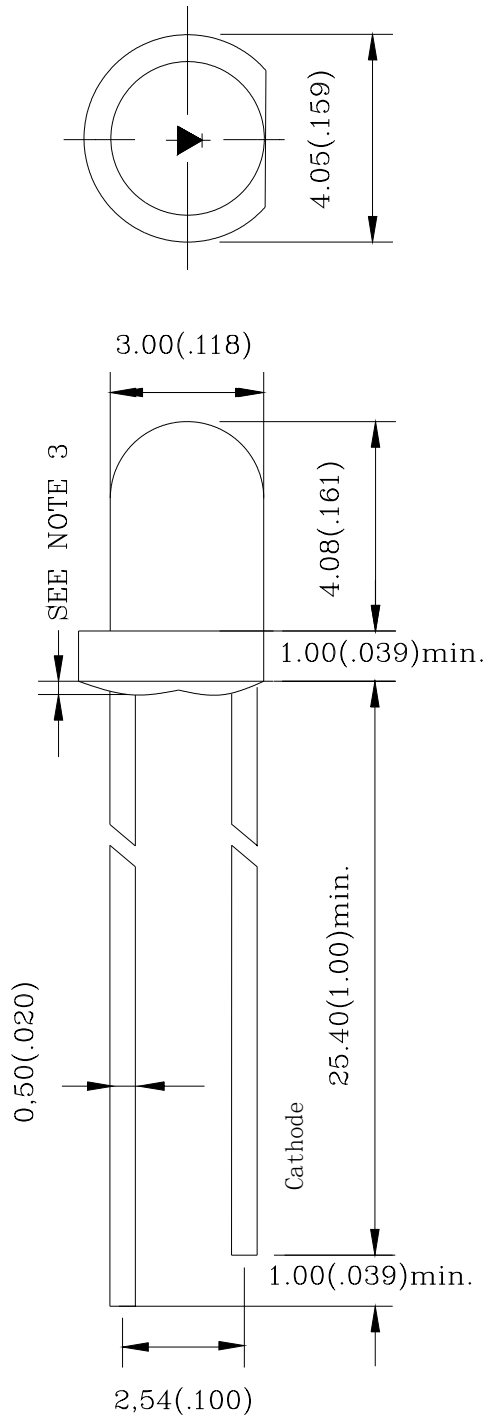
DATA SHEET

PART NO. : L34F3BT

3.0 mm INFRARED EMITTING DIODE

L34F3BT

PACKAGE DIMENSIONS



Note:

1.All Dimensions are in millimeters.
2.Tolerance is ±0.25mm(0.010 ")
Unless otherwise specified.
3.Protruded resin under flange
is 1.5mm(0.059 ") max.
4.Lead spacing is measured where
the leads emerge from the package.
5.Specification are subject to change
without notice

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L34F3BT

FEATURES

* EXTRA HIGH RADIANT POWER AND RADIANT INBTENSITY
* LOW FORWARD VOLTAGE
* SUITABLE FOR HIGH PULSE CURRENT OPERATIONTENSITY
* HIGH RELIABILITY
* Pb FREE PRODUCTS

CHIP MATERIALS

* Dice Material : GaAlAs/GaAs
* Lens Color : BLUE TRANSPARENT

ABSOLUTE MAXIMUM RATING : (Ta = 25°C)

SYMBOL	PARAMETER	INFRARED	UNIT
P_D	Power Dissipation	180	mW
V_R	Reverse Voltage	5	V
I_F	Average Forward Current	100	mA
I_{PF}	Peak forward current (F=1KHZ,duty=0.1)	800	mA
Topr	Operating Temperature Range	-35°C to 85°C	
Tstg	Storage Temperature Range	-35°C to 85°C	
Lead Soldering Temperature { 1.6mm(0.063 inch) From Body } 260°C ± 5°C for 5 Seconds			

ELECTRO-OPTICAL CHARACTERISTICS : (Ta = 25°C)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V_F	Forward Voltage	I_F = 20mA I_F = 100mA		1.3 1.5	 1.8	V
V_{FP}	Peak Forward Voltage	I_{PF}=800mA		2.2	2.5	V
I_R	Reverse Current	V_R = 5V			10	μA
λP	Peak Emission Wavelength	I_F = 20mA		940		nm
2θ1/2	Half Intensity Angle	I_F = 20mA		25		deg
I_E	Radiant Intensity	I_F = 20mA I_F=100mA		10 50		mw/sr

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